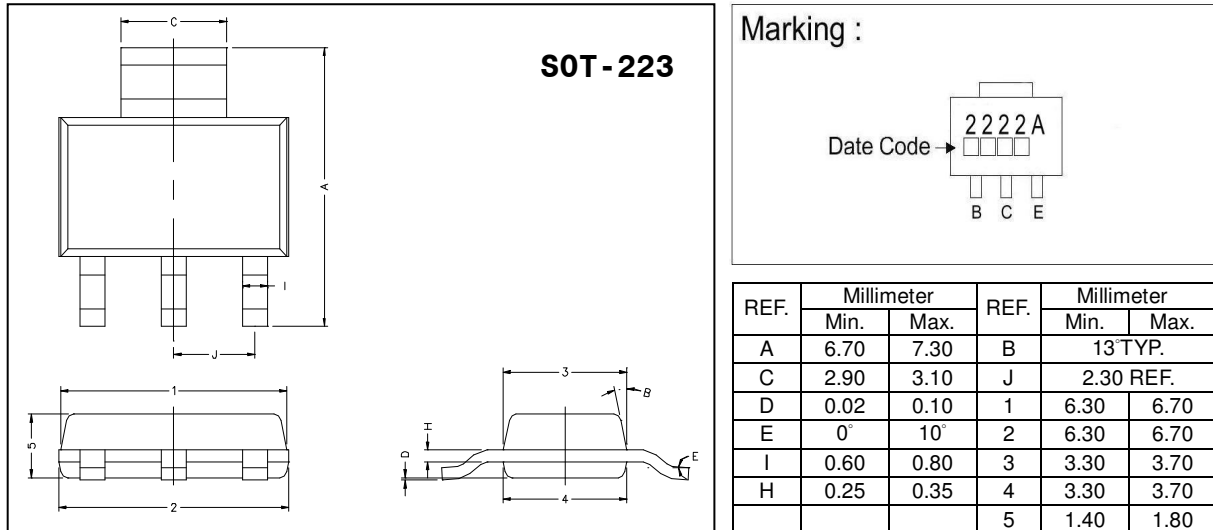


GL2222A NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GL2222A is designed for General Purpose Amplifier and High-Speed Switching, Medium-Power Switching Applications.

Package Dimensions



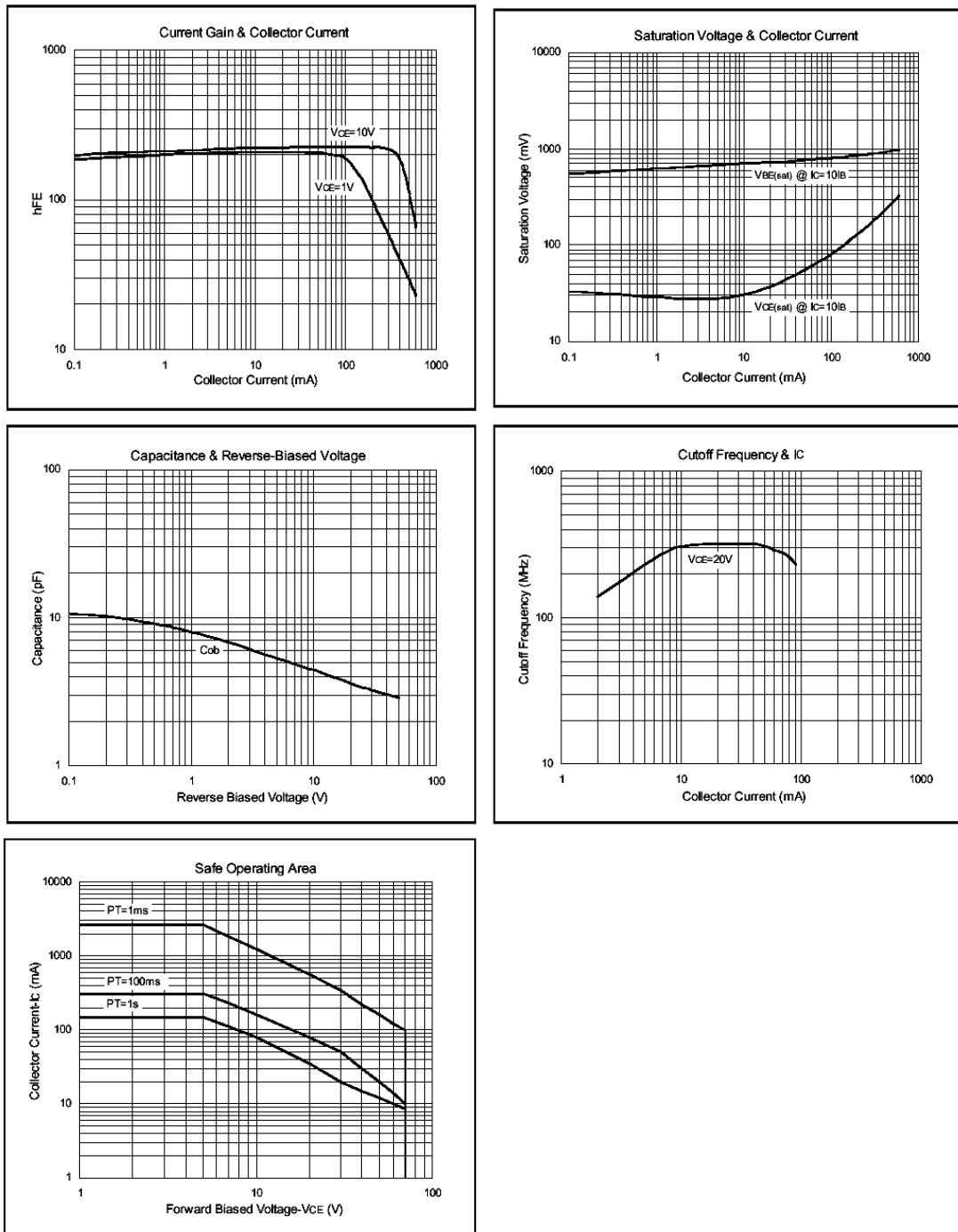
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	75	V
Collector to Emitter Voltage	VCEO	40	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	600	mA
Total Power Dissipation	PD	2	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	75	-	-	V	IC=100uA, IE=0
BVCEO	40	-	-	V	IC=10mA, IB=0
BVEBO	6	-	-	V	IE=10uA, IC=0
ICBO	-	-	10	nA	VCB=60V, IE=0
ICEX	-	-	10	nA	VCE=60V, VEB(OFF)=3V
IEBO	-	-	10	nA	VEB=3V
VCE(sat)1	-	-	500	mV	IC=380mA, IB=10mA
VCE(sat)2	-	-	1.0	V	IC=500mA, IB=50mA
VBE(sat)1	-	-	1.2	V	IC=150mA, IB=15mA
VBE(sat)2	-	-	2.0	V	IC=500mA, IB=50mA
hFE1	35	-	-		VCE=10V, IC=100uA
hFE2	50	-	-		VCE=10V, IC=1mA
hFE3	75	-	-		VCE=10V, IC=10mA
hFE4	100	-	300		VCE=10V, IC=150mA
Hfe5	40	-	-		VCE=10V, IC=500mA
fT	300	-	-	MHz	VCB=20V, IC=20mA, f=100MHz

Characteristics Curve



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